



New Sensors for Detectors

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Status Report

- XH : Germanium sensor on XSTRIP*
- 2d Microstructuring of Ge at CMF*
- Bump bonding and interconnect*

- GaAs tests (GESEC and OI)*
- Rad hard Si tests.*
- CZT material programme (PS)*

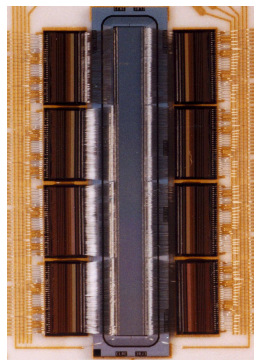


XH Germanium Sensor

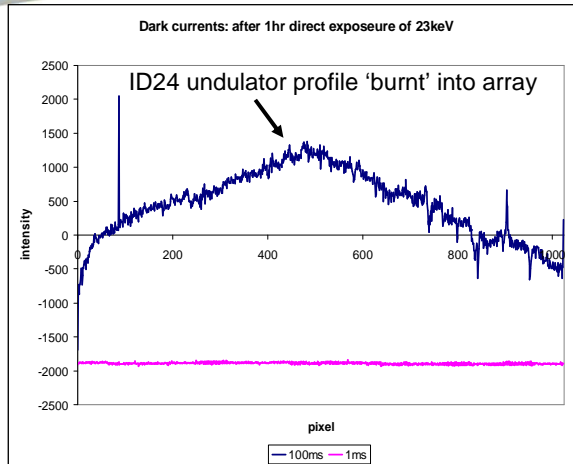
- XSTRIP system fine to 15keV.
- Radiation damage issues.
- Efficiency issues.
- Scattering issues.



XSTRIP - A detector for Energy Dispersive EXAFS



Custom designed
 μ strip: Si 500 μ m
thick, 1024 strips
on 25 μ m pitch
(CSNV)
8 x 128 channel
XCHIP ASICs.

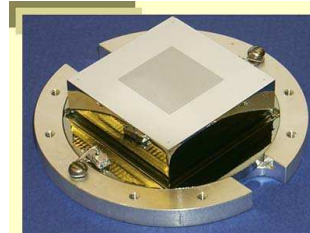
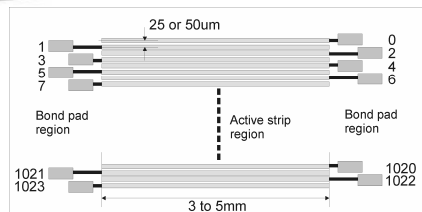
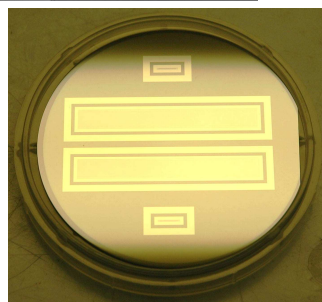
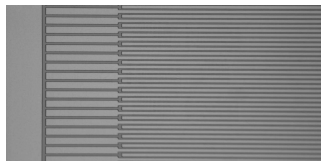


Surface oxide passivation charging at detector front surface causes localised breakdowns.

Limit to useful detector range to <15keV.

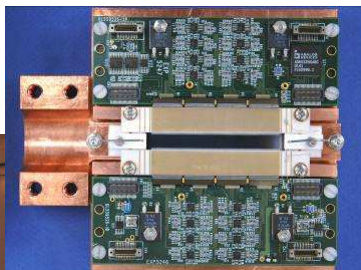


*XH – Fine pitch Ge.
Test wafer.
LBNL Technology*

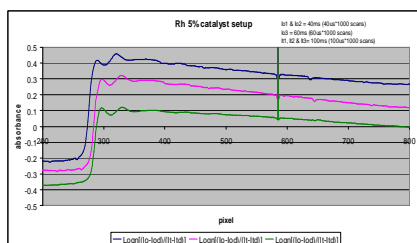
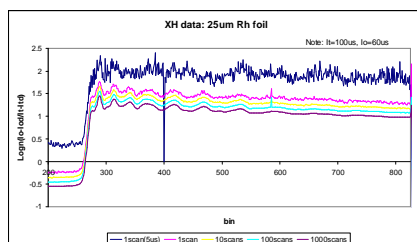


*RF sputtered a-Ge contact technology.
2d strip detectors demonstrated.
500um pitch pixels possible. NSS.*

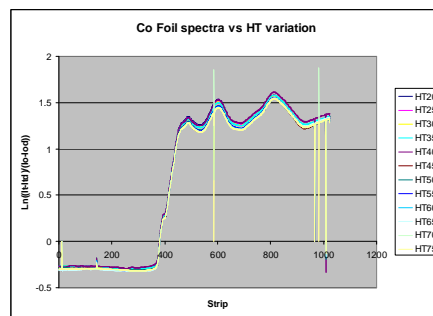
*XH : Worlds first fine pitch Ge
micro-strip for synchrotrons*



*Ge and ASIC/electronics thermally
separated.
10us readout as per XSTRIP
Initial tests on Station 9.3 SRS
Radiation hard.
Good efficiency and spatial
resolution.*



First XH data from ESRF and SRS
(Preliminary!)





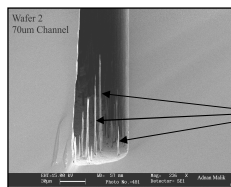
Ge microstructuring at CMF / STFC

Steps

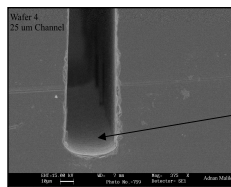
- *Structure material*
- *Model & fabricate true detectors*
- *Develop passivation.*
- *Develop interconnect*
- *Develop cooling and control*
- *Develop electronics*
- *Construct system*



Microstructuring @ CMF : GED



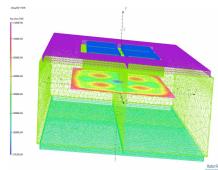
Grass



Smooth etch floor

- DRIE used for Ge structuring.
- Extensive modelling of pixel detectors ongoing.
- UK Commercial partners developing passivation technology.
- GeMOS transistors already in fabrication with QUB.
- Lithium implant being developed

- Goal to develop 2x2 HPGe pixel technology.





Interconnect technology

- Developing key capability
- Gold stud bumping completed
- Adhesive bumping trialled
- Indium bumping underway



Indium Bump Bonding



Indium Evaporator.
Wafer Size up to 200mm.

Goal : 172um initial
55um future.



Reflow Vacuum Hotplate
With Formic Acid Clean.
Wafer sizes up to 200mm.
On site, awaiting
installation.

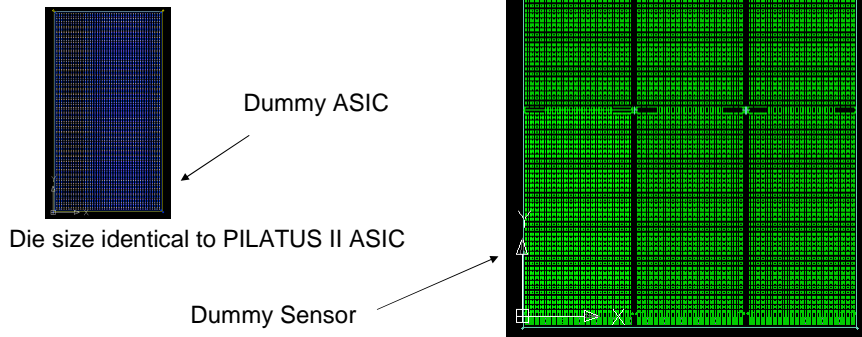


Suss-Microtec FC150
Installed & Tested



Suss-Microtec FC250
Awaiting installation

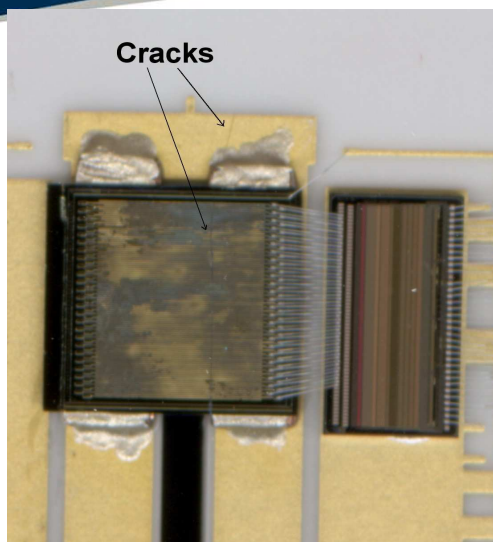
Daisy Chain Test Structure for Indium Bump Bonding Yield Tests



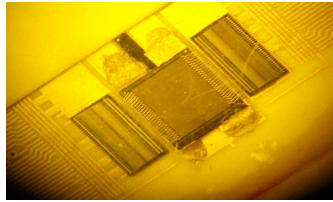
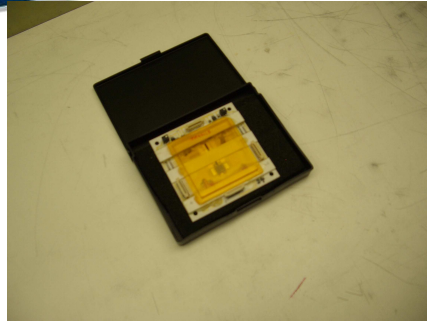
Wafer manufacture has been subcontracted to SemeFab.
CMF will evaporate indium through a lift off mask.
Reflow using Formic Acid reduction
Bump Bond using FC150

JRA #19 Goals

- Furthering Si damage tests and processing.
- Supporting edgeless silicon processing (Glasgow)
- Supporting Ge sensor processing.
- Supporting CZT sensor processing.
- Developing effective area cooling methods.
- Designing cooled ASICS.
- Scaling technologies.
- Evaluating sensors on SR (DLS).



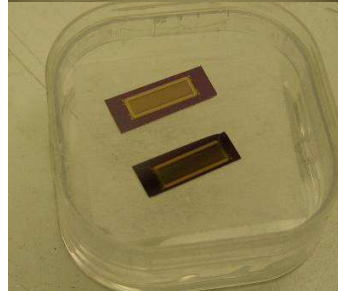
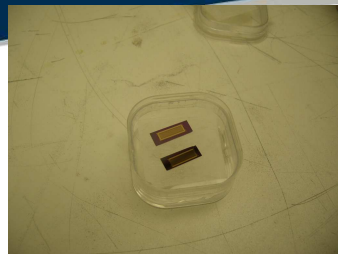
- 128 channels
- 25um pitch.
- 300um thickness !
- Initial bonding problems.



- Thickness issues.
- Initial tests inconclusive.
- Presently awaiting full tests.



GESEC Detector



- Material from GESEC Paris (Bourgoin)
- Active thickness unknown at present
- Masks and strip detector fabrication at University of Sheffield EPSRC III/V fab' plant.
- Presently awaiting full test.